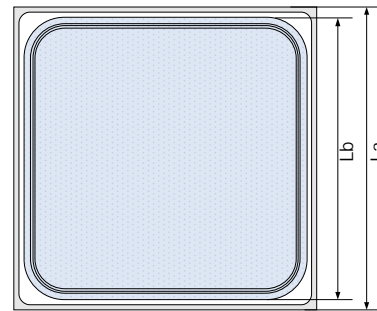


2SB183100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- ∅ 2SB183100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- ∅ Due to special schottky barrier structure, the chips have very low reverse leakage current (typical $I_R=0.002\text{mA}@ V_r=100\text{V}$) and maximum 150°C operation junction temperature;
- ∅ Low power losses, high efficiency;
- ∅ Guard ring construction for transient protection;
- ∅ High ESD capability;
- ∅ High surge capability;
- ∅ Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- ∅ Chip Size: 1830 μm X 1830 μm ;
- ∅ Chip Thickness: 280 \pm 20 μm ;
- ∅ Have two top side electrode materials for customer to choose, detail refer to ordering specifications.


Chip Topography and Dimensions
La: Chip Size: 1830 μm ;
Lb: Pad Size: 1730 μm ;
ORDERING SPECIFICATIONS

Product Name	Specification
2SB183100MAYY	For Axial leads package
2SB183100MAYL	For Au and AISi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	5	A
Peak Forward Surge Current@8.3ms	IFSM	150	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.5mA	100	--	V
Forward Voltage	VF	IF=5A	--	0.85	V
Reverse Current	IR	VR=100V	--	0.5	mA